5 key reasons

die-2-die interfaces need specialty I/O and **ESD**



'die-2-die' (D2D) interfaces operate outside the typical GPIO range

lower signal voltage & reduced drive current





For speed, D2D interfaces are designed with thin oxide transistors

> but those are easily damaged during ESD events





The parasitic capacitance of ESD protection in traditional GPIOs is too high

> for high bandwidth D2D interfaces





When chiplet applications target thousands of D2D connections

the standard I/O pads consume too much silicon area





ESD clamps integrated in traditional GPIOs are designed for >2kV HBM

while D2D interfaces only need a fraction of that.



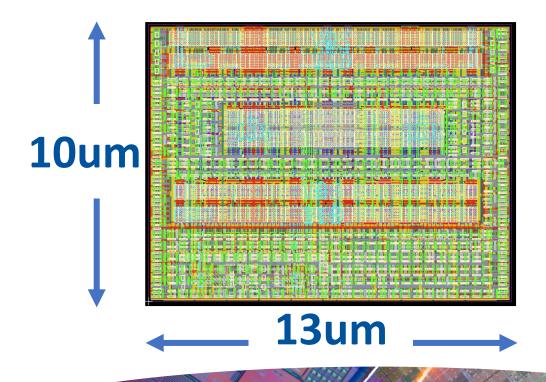
Sofics proven approach

- ESD protection of sensitive thin oxide circuits
- Protection for interfaces at 1V or lower
- ESD protection in smaller area
- Much reduced parasitic capacitance
- Scalable ESD robustness
- Proven on many fabs, processes



Example on 5nm FinFET

Full local protection for 0.9V I/O >100V HBM 14fF total capacitance





Reach out

- For more examples on other processes
- To discuss your project



Bart

